

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- High reliability

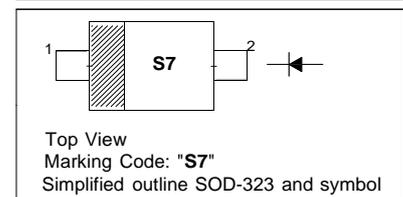
Applications

- Low current rectification

MARKING:S7

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|-----------------------------------------------|-----------|---------------|------------------|
| Peak Reverse Voltage | V_{RM} | 45 | V |
| Reverse Voltage | V_R | 40 | V |
| Mean Rectifying Current | I_O | 0.1 | A |
| Peak Forward Surge Current (60 Hz for 1 Cyc.) | I_{FSM} | 1 | A |
| Junction Temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 40 to + 125 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Typ. | Max. | Unit |
|------------------------------------------------------------------------------|--------|------|------|---------------|
| Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 10\text{ mA}$ | V_F | - | 0.55 | V |
| | V_F | - | 0.34 | V |
| Reverse Current at $V_R = 10\text{ V}$ | I_R | - | 30 | μA |
| Capacitance Between Terminals at $V_R = 10\text{ V}$, $f = 1\text{ MHz}$ | C_T | 6 | - | pF |

Note: ESD sensitive product handling required.

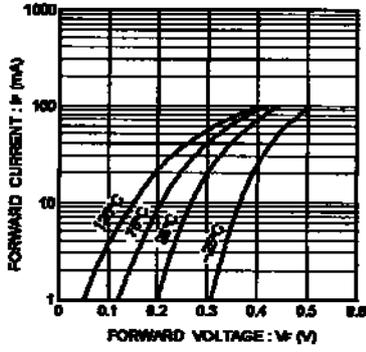


Fig. 1 Forward characteristics

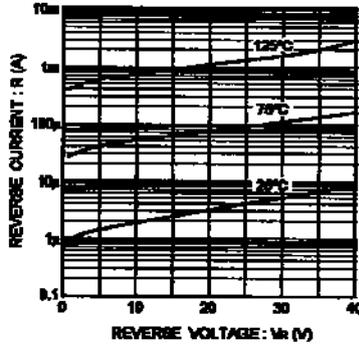


Fig. 2 Reverse characteristics

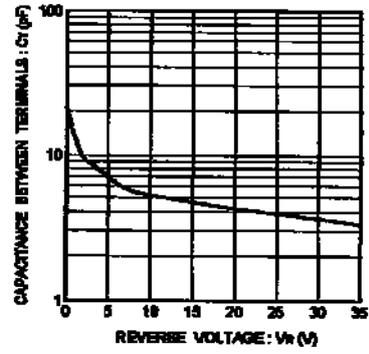
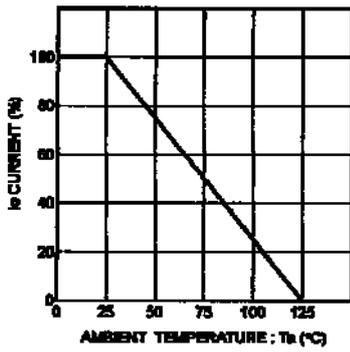


Fig. 3 Capacitance between terminals characteristics



**Fig. 4 Derating curve
(mounting on glass epoxy PCBs)**